

This data sheet is applicable to all TMS45160/Ps symbolized with Revision "D" and subsequent revisions as described on page 21.

- **Organization . . . 262144 × 16**
- **5-V Supply (±10% Tolerance)**
- **Performance Ranges:**

	ACCESS TIME	ACCESS TIME	ACCESS TIME	READ OR WRITE CYCLE MIN
	t _{RAC} MAX	t _{CAC} MAX	t _{AA} MAX	
'45160/P-60	60 ns	15 ns	30 ns	110 ns
'45160/P-70	70 ns	20 ns	35 ns	130 ns
'45160/P-80	80 ns	20 ns	40 ns	150 ns

- **Enhanced-Page-Mode Operation With xCAS-Before-RAS (xCBR) Refresh**
- **Long Refresh Period**
 - 512-Cycle Refresh in 8 ms (Max)**
 - 64 ms Max for Low Power With Self-Refresh Version (TMS45160P)**
- **3-State Unlatched Output**
- **Low Power Dissipation**
- **Texas Instruments EPIC™ CMOS Process**
- **All Inputs, Outputs, and Clocks Are TTL Compatible**
- **High-Reliability, 40-Lead, 400-Mil-Wide Plastic Surface-Mount (SOJ) Package and 40/44-Lead Thin Small-Outline Package (TSOP)**
- **Operating Free-Air Temperature Range 0°C to 70°C**
- **Low Power With Self-Refresh Version**
- **Upper and Lower Byte Control During Read and Write Operations**

DZ PACKAGE (TOP VIEW)						DGE PACKAGE (TOP VIEW)					
V _{CC}	1	40	V _{SS}			V _{CC}	1	44	V _{SS}		
DQ0	2	39	DQ15			DQ0	2	43	DQ15		
DQ1	3	38	DQ14			DQ1	3	42	DQ14		
DQ2	4	37	DQ13			DQ2	4	41	DQ13		
DQ3	5	36	DQ12			DQ3	5	40	DQ12		
V _{CC}	6	35	V _{SS}			V _{CC}	6	39	V _{SS}		
DQ4	7	34	DQ11			DQ4	7	38	DQ11		
DQ5	8	33	DQ10			DQ5	8	37	DQ10		
DQ6	9	32	DQ9			DQ6	9	36	DQ9		
DQ7	10	31	DQ8			DQ7	10	35	DQ8		
NC	11	30	NC								
NC	12	29	LCAS								
W	13	28	UCAS			NC	13	32	NC		
RAS	14	27	OE			NC	14	31	LCAS		
NC	15	26	A8			W	15	30	UCAS		
A0	16	25	A7			RAS	16	29	OE		
A1	17	24	A6			NC	17	28	A8		
A2	18	23	A5			A0	18	27	A7		
A3	19	22	A4			A1	19	26	A6		
V _{CC}	20	21	V _{SS}			A2	20	25	A5		
						A3	21	24	A4		
						V _{CC}	22	23	V _{SS}		

PIN NOMENCLATURE	
A0–A8	Address Inputs
DQ0–DQ15	Data In/Data Out
LCAS	Lower Column-Address Strobe
NC	No Internal Connection
OE	Output Enable
RAS	Row-Address Strobe
UCAS	Upper Column-Address Strobe
V _{CC}	5-V Supply
V _{SS}	Ground
W	Write Enable

description

The TMS45160 series are high-speed, 4194304-bit dynamic random-access memories organized as 262144 words of 16 bits each. The TMS45160P series are high-speed, low-power, self-refresh 4194304-bit dynamic random-access memories organized as 262144 words of 16 bits each. They employ state-of-the-art EPIC™ (Enhanced Performance Implanted CMOS) technology for high performance, reliability, and low power at low cost.

These devices feature maximum RAS access times of 60 ns, 70 ns, and 80 ns. Maximum power dissipation is as low as 770 mW operating and 11 mW standby on 80-ns devices. All inputs and outputs, including clocks, are compatible with Series 74 TTL. All addresses and data-in lines are latched on chip to simplify system design. Data out is unlatched to allow greater system flexibility.

The TMS45160 and TMS45160P are each offered in a 40-lead plastic surface-mount SOJ package (DZ suffix) and a 40/44-lead plastic surface-mount small-outline (TSOP) package (DGE suffix). These packages are characterized for operation from 0°C to 70°C.

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operation

dual $\overline{\text{CAS}}$

Two $\overline{\text{CAS}}$ pins ($\overline{\text{LCAS}}$ – $\overline{\text{UCAS}}$) are provided to give independent control of the 16 data I/O pins (DQ0–DQ15) with $\overline{\text{LCAS}}$ corresponding to DQ0–DQ7 and $\overline{\text{UCAS}}$ corresponding to DQ8–DQ15. For read or write cycles, the column address is latched on the first $\overline{\text{xCAS}}$ falling edge. Each $\overline{\text{xCAS}}$ going low enables its corresponding DQx pins with data associated with the column address latched on the first falling $\overline{\text{xCAS}}$ edge. All address setup and hold parameters are referenced to the first falling $\overline{\text{xCAS}}$ edge. The delay time from $\overline{\text{xCAS}}$ low to valid data out (see parameter t_{CAC}) is measured from each individual $\overline{\text{xCAS}}$ to its corresponding DQx pins.

In order to latch in a new column address, both $\overline{\text{xCAS}}$ pins must be brought high. The column precharge time (see parameter t_{CP}) is measured from the last $\overline{\text{xCAS}}$ rising edge to the first falling $\overline{\text{xCAS}}$ edge of the new cycle. Keeping a column address valid while toggling $\overline{\text{xCAS}}$ requires a minimum setup time, t_{CLCH} . During t_{CLCH} , at least one $\overline{\text{xCAS}}$ must be brought low before the other $\overline{\text{xCAS}}$ is taken high.

For early-write cycles, the data is latched on the first falling edge of $\overline{\text{xCAS}}$. Only the DQs that have the corresponding $\overline{\text{xCAS}}$ low are written into. Each $\overline{\text{xCAS}}$ must meet t_{CAS} minimum in order to ensure writing into the storage cell. In order to latch a new address and new data, both $\overline{\text{xCAS}}$ pins must go high and meet t_{CP} .

enhanced page mode

Page-mode operation allows faster memory access by keeping the same row address while selecting random column addresses. The time for row-address setup and hold and address multiplex is eliminated. The maximum number of columns that can be accessed is determined by the maximum $\overline{\text{RAS}}$ low time and the $\overline{\text{xCAS}}$ page-mode cycle time used. With minimum $\overline{\text{xCAS}}$ page cycle time, all 512 columns specified by column addresses A0 through A8 can be accessed without intervening $\overline{\text{RAS}}$ cycles.

Unlike conventional page-mode DRAMs, the column-address buffers in this device are activated on the falling edge of $\overline{\text{RAS}}$. The buffers act as transparent or flow-through latches while $\overline{\text{xCAS}}$ is high. The first falling edge of $\overline{\text{xCAS}}$ latches the column addresses. This feature allows the devices to operate at a higher data bandwidth than conventional page-mode parts because data retrieval begins as soon as column address is valid rather than when $\overline{\text{xCAS}}$ transitions low. This performance improvement is referred to as enhanced page mode. A valid column address can be presented immediately after t_{RAH} (row-address hold time) has been satisfied, usually well in advance of the falling edge of $\overline{\text{xCAS}}$. In this case, data is obtained after $t_{\text{CAC max}}$ (access time from $\overline{\text{xCAS}}$ low) if $t_{\text{AA max}}$ (access time from column address) has been satisfied. In the event that column addresses for the next page cycle are valid at the time $\overline{\text{xCAS}}$ goes high, minimum access time for the next cycle is determined by t_{CPA} (access time from rising edge of the last $\overline{\text{xCAS}}$).

address (A0–A8)

Eighteen address bits are required to decode 1 of 262144 storage cell locations. Nine row-address bits are set up on A0 through A8 and latched onto the chip by $\overline{\text{RAS}}$. Then, nine column-address bits are set up on A0 through A8 and latched onto the chip by the first $\overline{\text{xCAS}}$. All addresses must be stable on or before the falling edge of $\overline{\text{RAS}}$ and $\overline{\text{xCAS}}$. $\overline{\text{RAS}}$ is similar to a chip enable in that it activates the sense amplifiers as well as the row decoder. $\overline{\text{xCAS}}$ is used as a chip select, activating its corresponding output buffer and latching the address bits into the column-address buffers.

write enable ($\overline{\text{W}}$)

The read or write mode is selected through $\overline{\text{W}}$. A logic high on $\overline{\text{W}}$ selects the read mode and a logic low selects the write mode. $\overline{\text{W}}$ can be driven from the standard TTL circuits without a pullup resistor. The data input lines are disabled when the read mode is selected. When $\overline{\text{W}}$ goes low prior to $\overline{\text{xCAS}}$ (early write), data out remains in the high-impedance state for the entire cycle, permitting a write operation with OE grounded.

data in (DQ0–DQ15)

Data is written during a write or read-modify-write cycle. Depending on the mode of operation, the falling edge of $\overline{\text{xCAS}}$ or $\overline{\text{W}}$ strobes data into the on-chip data latch. In an early-write cycle, $\overline{\text{W}}$ is brought low prior to $\overline{\text{xCAS}}$ and the data is strobed in by the first occurring $\overline{\text{xCAS}}$ with setup and hold times referenced to data in. In a delayed-write or read-modify-write cycle, $\overline{\text{xCAS}}$ is already low and the data is strobed in by $\overline{\text{W}}$ with setup and hold times referenced to data in. In a delayed-write or read-modify-write cycle, $\overline{\text{OE}}$ must be high to bring the output buffers to the high-impedance state prior to impressing data on the I/O lines.

data out (DQ0–DQ15)

The 3-state output buffer provides direct TTL compatibility (no pullup resistor required) with a fanout of two Series 74 TTL loads. Data out is the same polarity as data in. The output is in the high-impedance (floating) state until $\overline{\text{xCAS}}$ and $\overline{\text{OE}}$ are brought low. In a read cycle, the output becomes valid after the access-time interval t_{CAC} (which begins with the negative transition of $\overline{\text{xCAS}}$) as long as t_{RAC} and t_{AA} are satisfied.

output enable ($\overline{\text{OE}}$)

$\overline{\text{OE}}$ controls the impedance of the output buffers. When $\overline{\text{OE}}$ is high, the buffers remain in the high-impedance state. Bringing $\overline{\text{OE}}$ low during a normal cycle activates the output buffers, putting them in the low-impedance state. It is necessary for both $\overline{\text{RAS}}$ and $\overline{\text{xCAS}}$ to be brought low for the output buffers to go into the low-impedance state. They remain in the low-impedance state until either $\overline{\text{OE}}$ or $\overline{\text{xCAS}}$ is brought high.

$\overline{\text{RAS}}$ -only refresh

A refresh operation must be performed at least once every 8 ms (64 ms for TMS45160P) to retain data. This can be achieved by strobing each of the 512 rows (A0–A8). A normal read or write cycle refreshes all bits in each row that is selected. A $\overline{\text{RAS}}$ -only operation can be used by holding all $\overline{\text{xCAS}}$ at the high (inactive) level, conserving power as the output buffers remain in the high-impedance state. Externally generated addresses must be used for a $\overline{\text{RAS}}$ -only refresh.

hidden refresh

Hidden refresh can be performed while maintaining valid data at the output pin. This is accomplished by holding $\overline{\text{xCAS}}$ at V_{IL} after a read operation and cycling $\overline{\text{RAS}}$ after a specified precharge period, similar to a $\overline{\text{RAS}}$ -only refresh cycle. The external address is ignored and the refresh address is generated internally.

$\overline{\text{xCAS}}$ -before- $\overline{\text{RAS}}$ (xCBR) refresh

xCBR refresh is utilized by bringing at least one $\overline{\text{xCAS}}$ low earlier than $\overline{\text{RAS}}$ (see parameter t_{CSR}) and holding it low after $\overline{\text{RAS}}$ falls (see parameter t_{CHR}). For successive xCBR refresh cycles, $\overline{\text{xCAS}}$ can remain low while cycling $\overline{\text{RAS}}$. The external address is ignored and the refresh address is generated internally.

A low-power battery-backup refresh mode that requires less than 500- μA refresh current is available on the TMS45160P. Data integrity is maintained using xCBR refresh with a period of 125 μs holding $\overline{\text{RAS}}$ low for less than 1 μs . To minimize current consumption, all input levels must be at CMOS levels ($V_{\text{IL}} \leq 0.2 \text{ V}$, $V_{\text{IH}} \geq V_{\text{CC}} - 0.2 \text{ V}$).

self refresh (TMS45160P)

The self-refresh mode is entered by dropping $\overline{\text{xCAS}}$ low prior to $\overline{\text{RAS}}$ going low. Then $\overline{\text{xCAS}}$ and $\overline{\text{RAS}}$ are both held low for a minimum of 100 μs . The chip is refreshed internally by an on-board oscillator. No external address is required since the CBR counter is used to keep track of the address. To exit the self-refresh mode, both $\overline{\text{RAS}}$ and $\overline{\text{xCAS}}$ are brought high to satisfy t_{CHS} . Upon exiting the self-refresh mode, a burst refresh (refresh a full set of row addresses) must be executed before continuing with normal operation. This ensures that the DRAM is fully refreshed.

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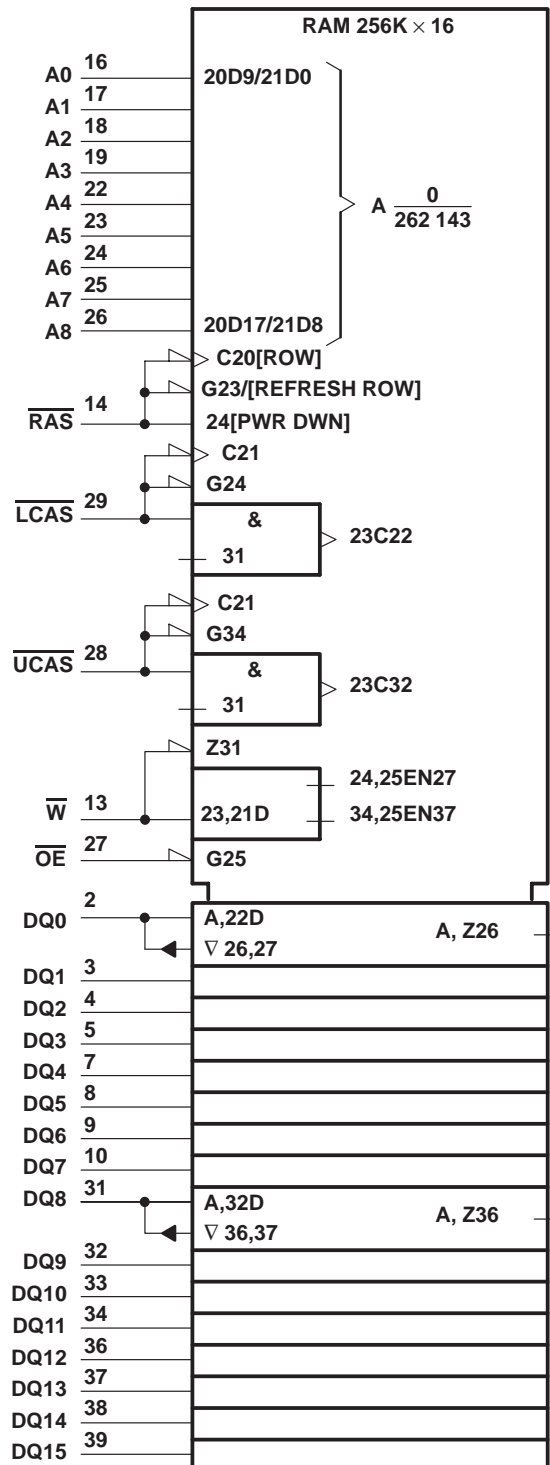
power up

To achieve proper device operation, an initial pause of 200 μ s followed by a minimum of eight $\overline{\text{RAS}}$ cycles is required after power up to the full V_{CC} level. These eight initialization cycles must include at least one refresh ($\overline{\text{RAS}}$ -only or xCBR) cycle.



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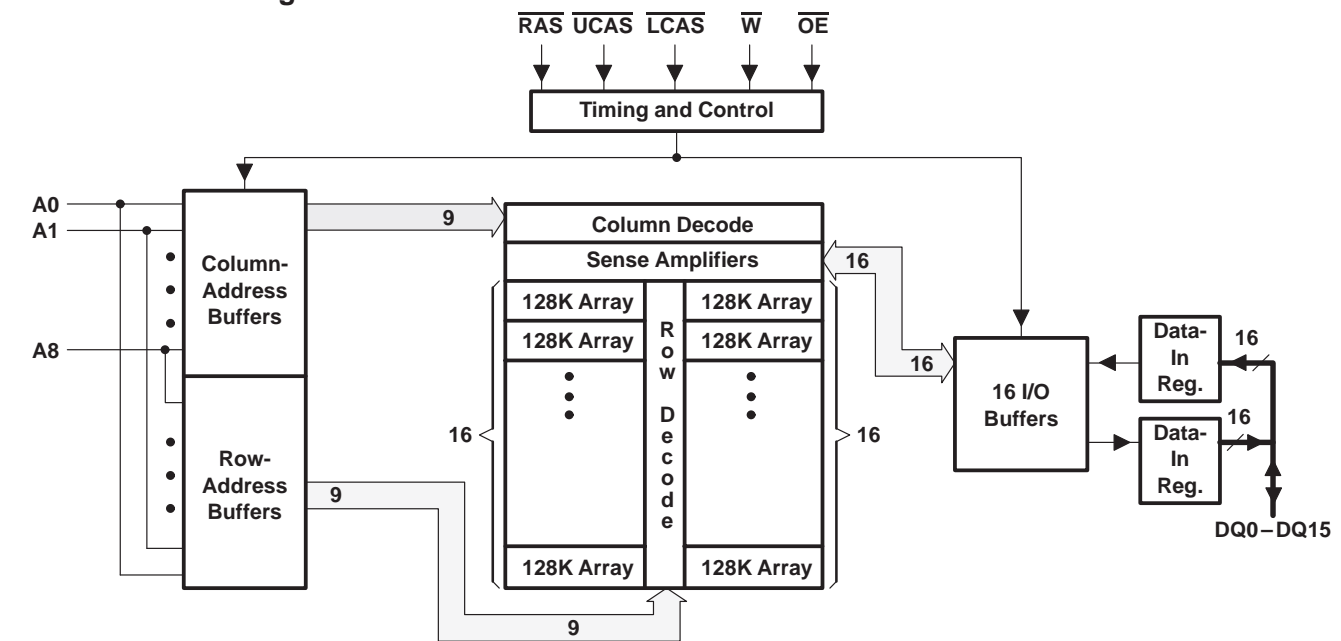
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
The pin numbers shown are for the DZ package.

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functional block diagram



- absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]
- Supply voltage range, V_{CC} - 1 V to 7 V
 - Voltage range on any pin (see Note 1) - 1 V to 7 V
 - Short-circuit output current 50 mA
 - Power dissipation 1 W
 - Operating free-air temperature range, T_A 0°C to 70°C
 - Storage temperature range, T_{stg} - 55°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to V_{SS} .

recommended operating conditions

	MIN	NOM	MAX	UNIT
V_{CC} Supply voltage	4.5	5	5.5	V
V_{SS} Supply voltage		0		V
V_{IH} High-level input voltage	2.4		6.5	V
V_{IL} Low-level input voltage (see Note 2)	- 1		0.8	V
T_A Operating free-air temperature	0		70	°C

NOTE 2: The algebraic convention, where the more negative (less positive) limit is designated as minimum, is used for logic-voltage levels only.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	'45160-60 '45160P-60		'45160-70 '45160P-70		'45160-80 '45160P-80		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage I _{OH} = – 5 mA	2.4		2.4		2.4		V
V _{OL}	Low-level output voltage I _{OL} = 4.2 mA		0.4		0.4		0.4	V
I _I	Input current (leakage) V _{CC} = 5.5 V, V _I = 0 V to 6.5 V, All others = 0 V to V _{CC}		± 10		± 10		± 10	µA
I _O	Output current (leakage) V _{CC} = 5.5 V, V _O = 0 V to V _{CC} , CAS high		± 10		± 10		± 10	µA
I _{CC1} †§	Read- or write-cycle current V _{CC} = 5.5 V, Minimum cycle		180		160		140	mA
I _{CC2}	Standby current V _{IH} = 2.4 V (TTL), After 1 memory cycle, RAS and xCAS high		2		2		2	mA
I _{CC2}	Standby current V _{IH} = V _{CC} – 0.2 V (CMOS), After 1 memory cycle, RAS and xCAS high	'45160	1		1		1	mA
		'45160P	350		350		350	µA
I _{CC3} ‡	Average refresh current (RAS-only refresh or CBR) V _{CC} = 5.5 V, Minimum cycle, (RAS only), RAS cycling, xCAS high (CBR only), RAS low after xCAS low		180		160		140	mA
I _{CC4} †§	Average page current V _{CC} = 5.5 V, t _{PC} = MIN, RAS low, xCAS cycling		160		140		120	mA
I _{CC5} ¶	Battery-backup operating current (equivalent refresh time is 64 ms); CBR only t _{RC} = 125 µs, t _{RAS} ≤ 1 µs, V _{CC} – 0.2 V ≤ V _{IH} ≤ 6.5 V, 0 V ≤ V _{IL} ≤ 0.2 V, W and OE = V _{IH} , Address and data stable		500		500		500	µA
I _{CC6} †¶	Self-refresh current xCAS < 0.2 V, RAS < 0.2 V, t _{RAS} and t _{CAS} > 1000 ms		400		400		400	µA

† Measured with outputs open

‡ Measured with a maximum of one address change while $\overline{\text{RAS}} = V_{IL}$

§ Measured with a maximum of one address change while $\text{xCAS} = V_{IH}$

¶ For TMS45160P only

capacitance over recommended ranges of supply voltage and operating free-air temperature, f = 1 MHz[#] (see Note 3)

PARAMETER		MIN	MAX	UNIT
C _{i(A)}	Input capacitance, A0–A8		5	pF
C _{i(OE)}	Input capacitance, $\overline{\text{OE}}$		7	pF
C _{i(RC)}	Input capacitance, $\overline{\text{xCAS}}$ and $\overline{\text{RAS}}$		7	pF
C _{i(W)}	Input capacitance, $\overline{\text{W}}$		7	pF
C _O	Output capacitance		7	pF

[#] Capacitance measurements are made on a sample basis only.

NOTE 3: V_{CC} = 5 V ± 0.5 V, and the bias on pins under test is 0 V.



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature

PARAMETER	'45160-60 '45160P-60		'45160-70 '45160P-70		'45160-80 '45160P-80		UNIT
	MIN	MAX	MIN	MAX	MIN	MAX	
t _{CAC} Access time from $\overline{\text{xCAS}}$ low		15		20		20	ns
t _{AA} Access time from column address		30		35		40	ns
t _{RAC} Access time from $\overline{\text{RAS}}$ low		60		70		80	ns
t _{OEa} Access time from $\overline{\text{OE}}$ low		15		20		20	ns
t _{CPA} Access time from column precharge		35		40		45	ns
t _{CLZ} Delay time, $\overline{\text{xCAS}}$ low to output in low impedance	0		0		0		ns
t _{OFF} Output disable time after $\overline{\text{xCAS}}$ high (see Note 4)	0	15	0	20	0	20	ns
t _{OEZ} Output disable time after $\overline{\text{OE}}$ high (see Note 4)	0	15	0	20	0	20	ns

NOTE 4: t_{OFF} and t_{OEZ} are specified when the output is no longer driven.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (see Note 5)

	'45160-60 '45160P-60		'45160-70 '45160P-70		'45160-80 '45160P-80		UNIT
	MIN	MAX	MIN	MAX	MIN	MAX	
t _{RC} Cycle time, read (see Note 6)		110		130		150	ns
t _{WC} Cycle time, write		110		130		150	ns
t _{RWC} Cycle time, read-write/read-modify-write		155		185		205	ns
t _{PC} Cycle time, page-mode read or write (see Note 7)		40		45		50	ns
t _{PRWC} Cycle time, page-mode read-modify-write		85		90		105	ns
t _{RASP} Pulse duration, $\overline{\text{RAS}}$ low, page mode (see Note 8)	60	100 000	70	100 000	80	100 000	ns
t _{RAS} Pulse duration, $\overline{\text{RAS}}$ low, nonpage mode (see Note 8)	60	10 000	70	10 000	80	10 000	ns
t _{CAS} Pulse duration, $\overline{\text{xCAS}}$ low (see Note 9)	15	10 000	20	10 000	20	10 000	ns
t _{CP} Pulse duration, $\overline{\text{xCAS}}$ high	10		10		10		ns
t _{RP} Pulse duration, $\overline{\text{RAS}}$ high (precharge)	40		50		60		ns
t _{WP} Pulse duration, write	15		15		15		ns
t _{ASC} Setup time, column address before $\overline{\text{xCAS}}$ low	0		0		0		ns
t _{ASR} Setup time, row address before $\overline{\text{RAS}}$ low	0		0		0		ns
t _{DS} Setup time, data before $\overline{\text{W}}$ low (see Note 10)	0		0		0		ns
t _{RCS} Setup time, read before $\overline{\text{xCAS}}$ low	0		0		0		ns
t _{CWL} Setup time, $\overline{\text{W}}$ low before $\overline{\text{xCAS}}$ high	15		20		20		ns
t _{RWL} Setup time, $\overline{\text{W}}$ low before $\overline{\text{RAS}}$ high	15		20		20		ns
t _{WCS} Setup time, $\overline{\text{W}}$ low before $\overline{\text{xCAS}}$ low (see Note 11)	0		0		0		ns

- NOTES: 5. Timing measurements are referenced to V_{IL} max and V_{IH} min.
6. All cycle times assume t_T = 5 ns.
7. To assure t_{PC} min, t_{ASC} should be ≥ t_{CP}.
8. In a read-modify-write cycle, t_{RWD} and t_{RWL} must be observed.
9. In a read-modify-write cycle, t_{CWD} and t_{CWL} must be observed.
10. Referenced to the later of $\overline{\text{xCAS}}$ or $\overline{\text{W}}$ in write operations
11. Early-write operation only



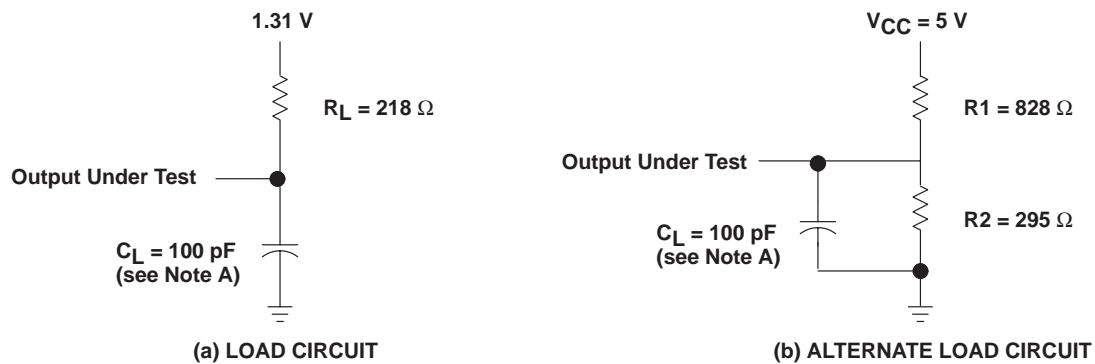
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timing requirements over recommended ranges of supply voltage and operating free-air temperature (continued) (see Note 5)

		'45160-60 '45160P-60		'45160-70 '45160P-70		'45160-80 '45160P-80		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{CAH}	Hold time, column address after $\overline{\text{xCAS}}$ low (see Note 10)	10		15		15		ns
t _{DHR}	Hold time, data after $\overline{\text{RAS}}$ low (see Note 12)	30		35		35		ns
t _{DH}	Hold time, data after $\overline{\text{xCAS}}$ low (see Note 10)	10		15		15		ns
t _{AR}	Hold time, column address after $\overline{\text{RAS}}$ low (see Note 12)	30		35		35		ns
t _{RAH}	Hold time, row address after $\overline{\text{RAS}}$ low	10		10		10		ns
t _{RCH}	Hold time, read after $\overline{\text{xCAS}}$ high (see Note 13)	0		0		0		ns
t _{RRH}	Hold time, read after $\overline{\text{RAS}}$ high (see Note 13)	0		0		0		ns
t _{WCH}	Hold time, write after $\overline{\text{xCAS}}$ low (see Note 13)	10		15		15		ns
t _{WCR}	Hold time, write after $\overline{\text{RAS}}$ low (see Note 14)	30		35		35		ns
t _{CLCH}	Hold time, $\overline{\text{xCAS}}$ low to $\overline{\text{xCAS}}$ high	5		5		5		ns
t _{AWD}	Delay time, column address to $\overline{\text{W}}$ low (see Note 15)	55		65		70		ns
t _{CHR}	Delay time, $\overline{\text{RAS}}$ low to $\overline{\text{xCAS}}$ high (see Note 11)	15		15		20		ns
t _{CRP}	Delay time, $\overline{\text{xCAS}}$ high to $\overline{\text{RAS}}$ low	0		0		0		ns
t _{CSH}	Delay time, $\overline{\text{RAS}}$ low to $\overline{\text{xCAS}}$ high	60		70		80		ns
t _{CSR}	Delay time, $\overline{\text{xCAS}}$ low to $\overline{\text{RAS}}$ low (see Note 11)	10		10		10		ns
t _{CWD}	Delay time, $\overline{\text{xCAS}}$ low to $\overline{\text{W}}$ low (see Note 15)	40		50		50		ns
t _{OEH}	Hold time, $\overline{\text{OE}}$ command	15		20		20		ns
t _{OED}	Delay time, $\overline{\text{OE}}$ high before data at DQ	15		20		20		ns
t _{ROH}	Delay time, $\overline{\text{OE}}$ low to $\overline{\text{RAS}}$ high	10		10		10		ns
t _{RAD}	Delay time, $\overline{\text{RAS}}$ low to column address (see Note 16)	15	30	15	35	15	40	ns
t _{RAL}	Delay time, column address to $\overline{\text{RAS}}$ high	30		35		40		ns
t _{CAL}	Delay time, column address to $\overline{\text{xCAS}}$ high	30		35		40		ns
t _{RCD}	Delay time, $\overline{\text{RAS}}$ low to $\overline{\text{xCAS}}$ low (see Note 16)	20	45	20	50	20	60	ns
t _{RPC}	Delay time, $\overline{\text{RAS}}$ high to $\overline{\text{xCAS}}$ low (see Note 11)	0		0		0		ns
t _{RSH}	Delay time, $\overline{\text{xCAS}}$ low to $\overline{\text{RAS}}$ high	15		20		20		ns
t _{RWD}	Delay time, $\overline{\text{RAS}}$ low to $\overline{\text{W}}$ low (see Note 15)	85		100		110		ns
t _{CPR}	Pulse duration, $\overline{\text{xCAS}}$ precharge before self refresh	0		0		0		ns
t _{RPS}	Pulse duration, $\overline{\text{RAS}}$ precharge after self refresh	110		130		150		ns
t _{RASS}	Pulse duration, self refresh entry from $\overline{\text{RAS}}$ low	100		100		100		μs
t _{CHS}	Hold time, $\overline{\text{xCAS}}$ low after $\overline{\text{RAS}}$ high (for self refresh)	– 50		– 50		– 50		ns
t _{REF}	Refresh time interval	'45160	8	'45160	8	'45160	8	ms
		'45160P	64	'45160P	64	'45160P	64	
t _T	Transition time	2	50	2	50	2	50	ns

- NOTES: 5. Timing measurements are referenced to V_{IL} max and V_{IH} min.
10. Referenced in the later of $\overline{\text{xCAS}}$ or $\overline{\text{W}}$ in write operations.
11. Early-write operation only
12. The minimum value is measured when t_{RCD} is set to t_{RCD} min as a reference.
13. Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.
14. xCBR refresh only
15. Read-modify-write operation only
16. Maximum value specified only to assure access time

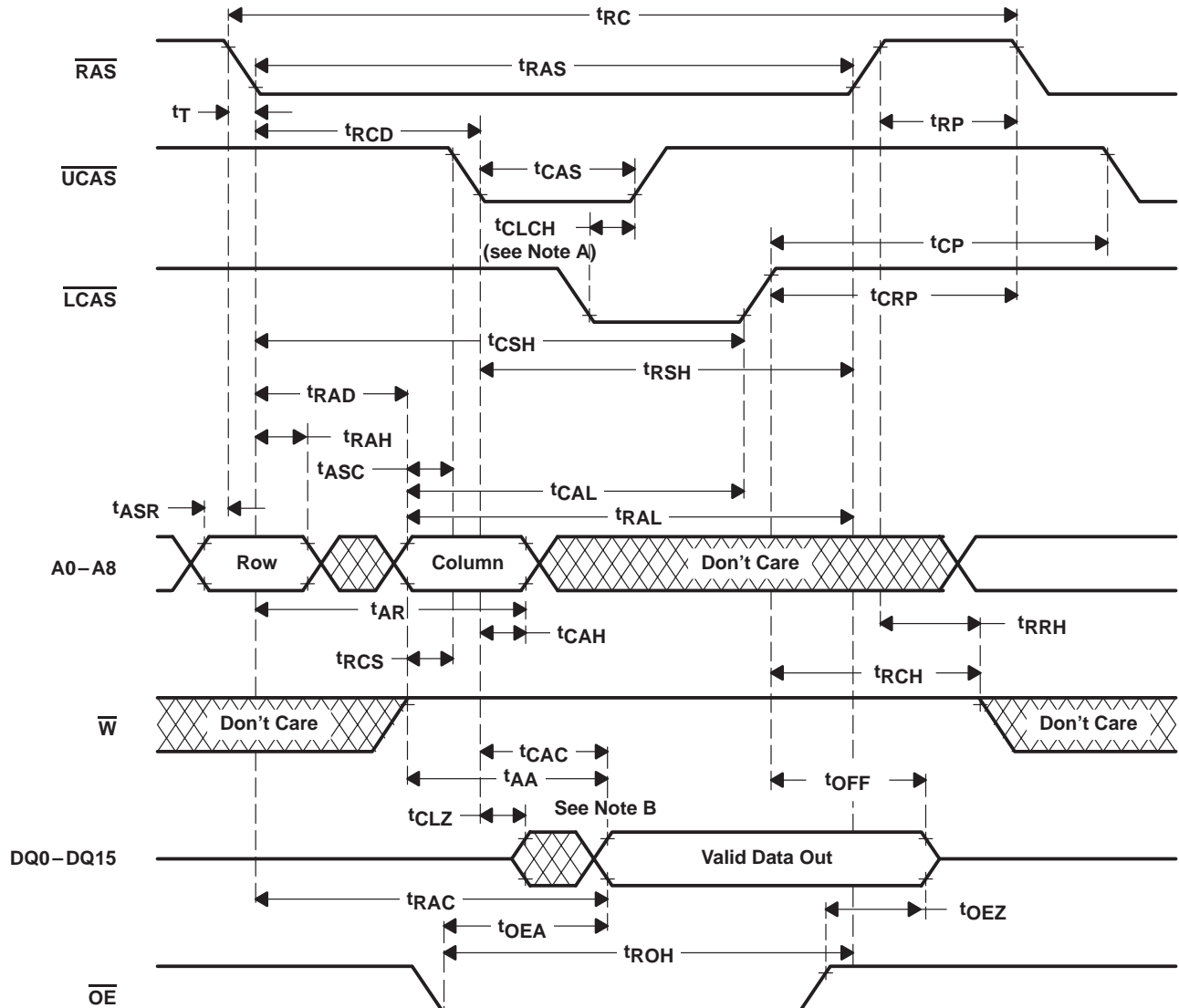
PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes probe and fixture capacitance.

Figure 1. Load Circuits for Timing Parameters

PARAMETER MEASUREMENT INFORMATION



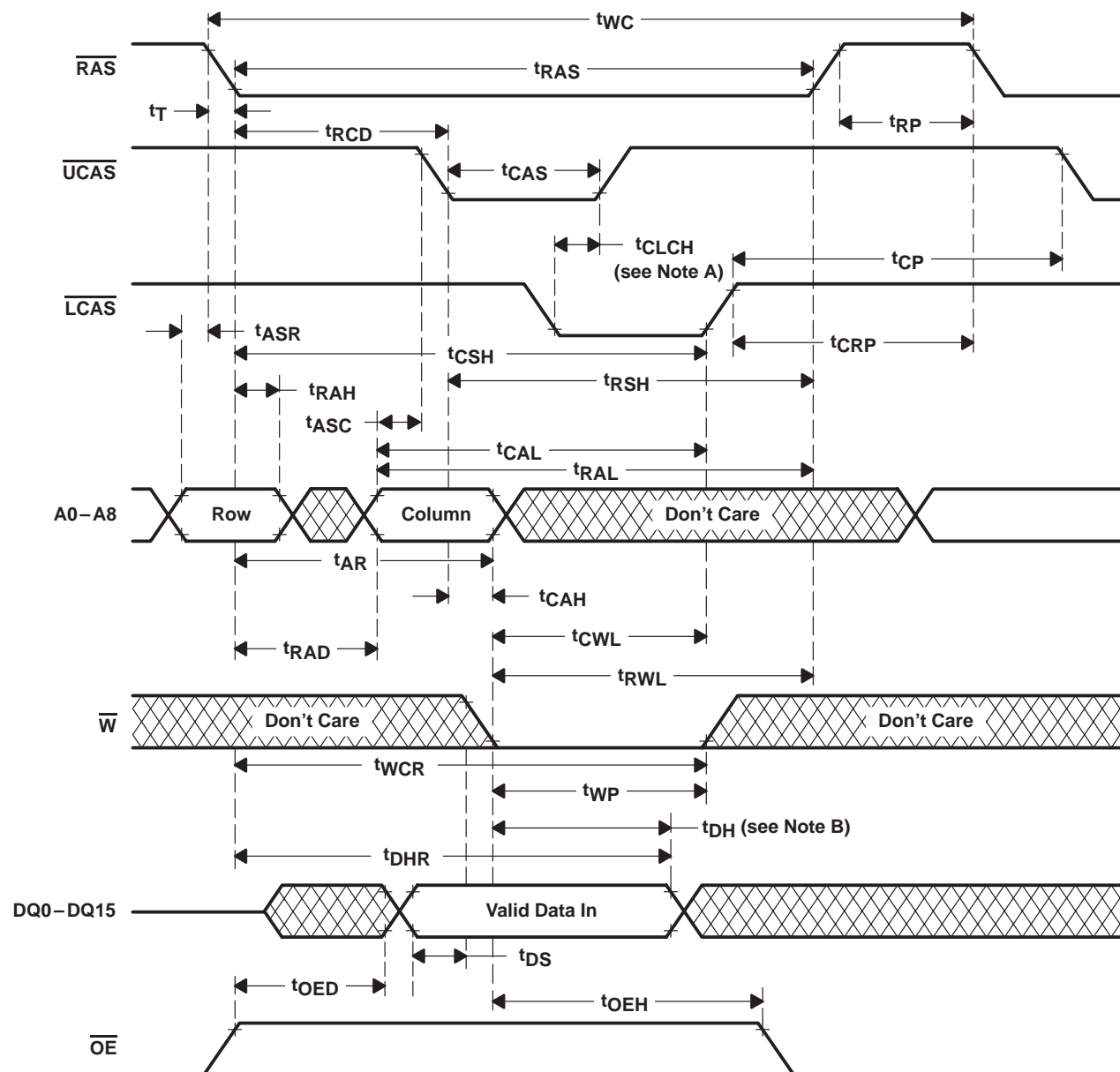
- NOTES: A. In order to hold the address latched by the first $\overline{\text{xCAS}}$ going low, the parameter t_{CLCH} must be met.
B. Output can go from the high-impedance state to an invalid-data state prior to the specified access time.
C. t_{CAC} is measured from $\overline{\text{xCAS}}$ to its corresponding DQx .
D. $\overline{\text{xCAS}}$ order is arbitrary.

Figure 2. Read-Cycle Timing

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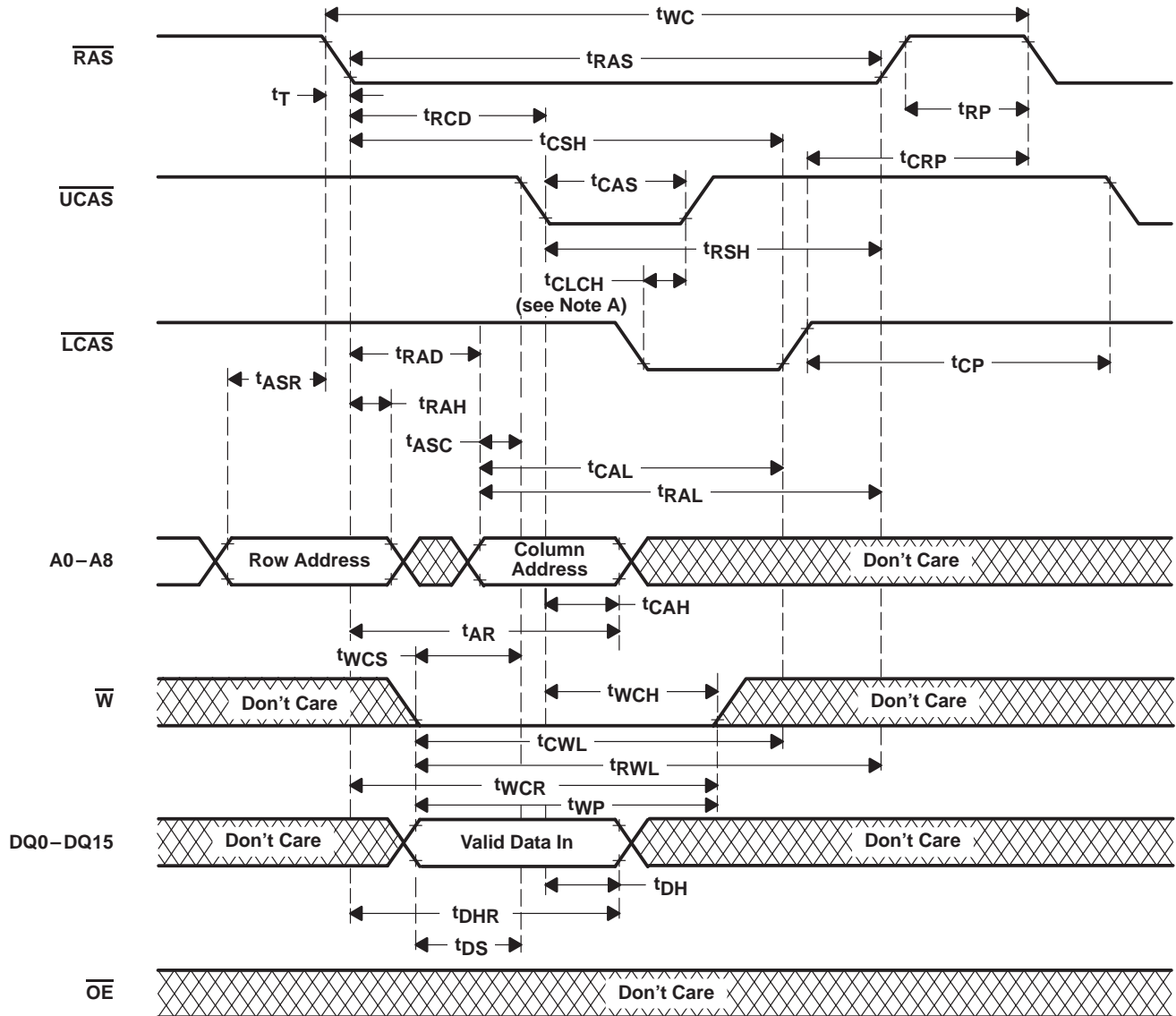
- NOTES: A. In order to hold the address latched by the first $\overline{\text{xCAS}}$ going low, the parameter t_{CLCH} must be met.
 B. Later of $\overline{\text{xCAS}}$ or $\overline{\text{W}}$ in write operations
 C. $\overline{\text{xCAS}}$ order is arbitrary.

Figure 3. Write-Cycle Timing



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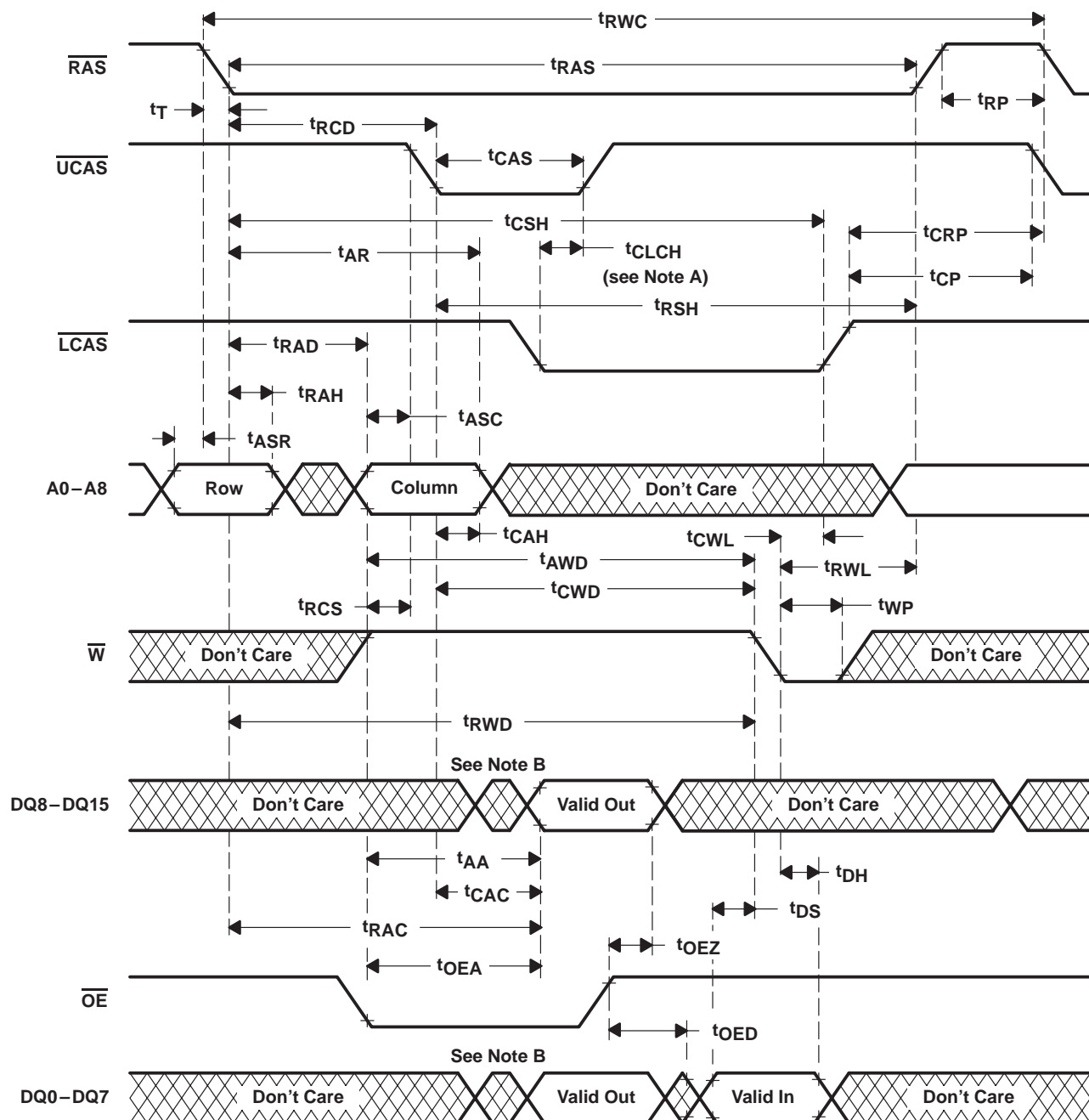
PARAMETER MEASUREMENT INFORMATION



NOTES: A. In order to hold the address latched by the first \overline{xCAS} going low, the parameter t_{CLCH} must be met.
B. \overline{xCAS} order is arbitrary.

Figure 4. Early-Write-Cycle Timing

PARAMETER MEASUREMENT INFORMATION



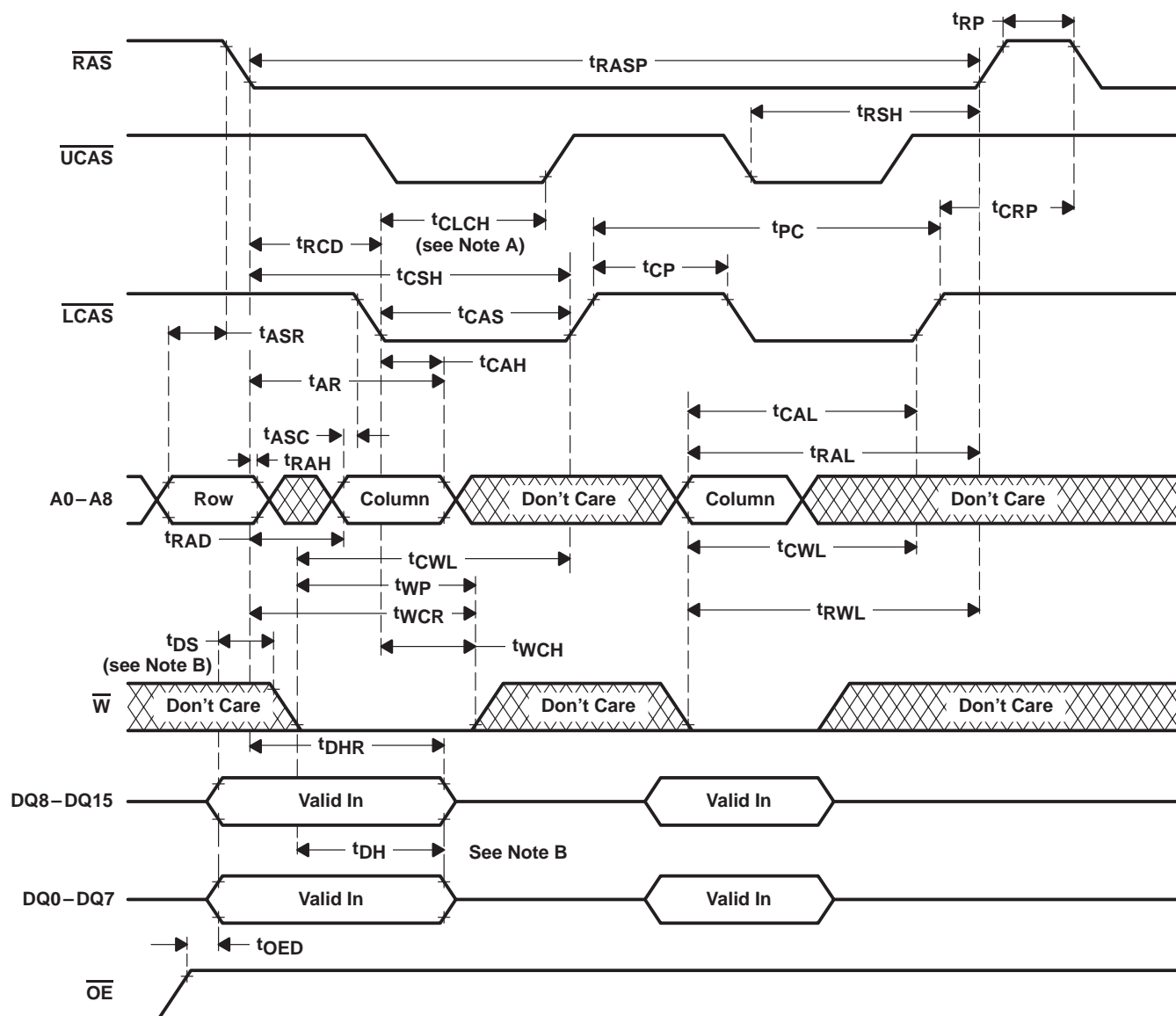
- NOTES: A. In order to hold the address latched by the first xCAS going low, the parameter t_{CLCH} must be met.
B. Output can go from the high-impedance state to an invalid-data state prior to the specified access time.
C. xCAS order is arbitrary.

Figure 5. Read-Modify-Write-Cycle Timing

[illegible]

- ### Figure 6. Enhanced-Page-Mode Read-Cycle Timing

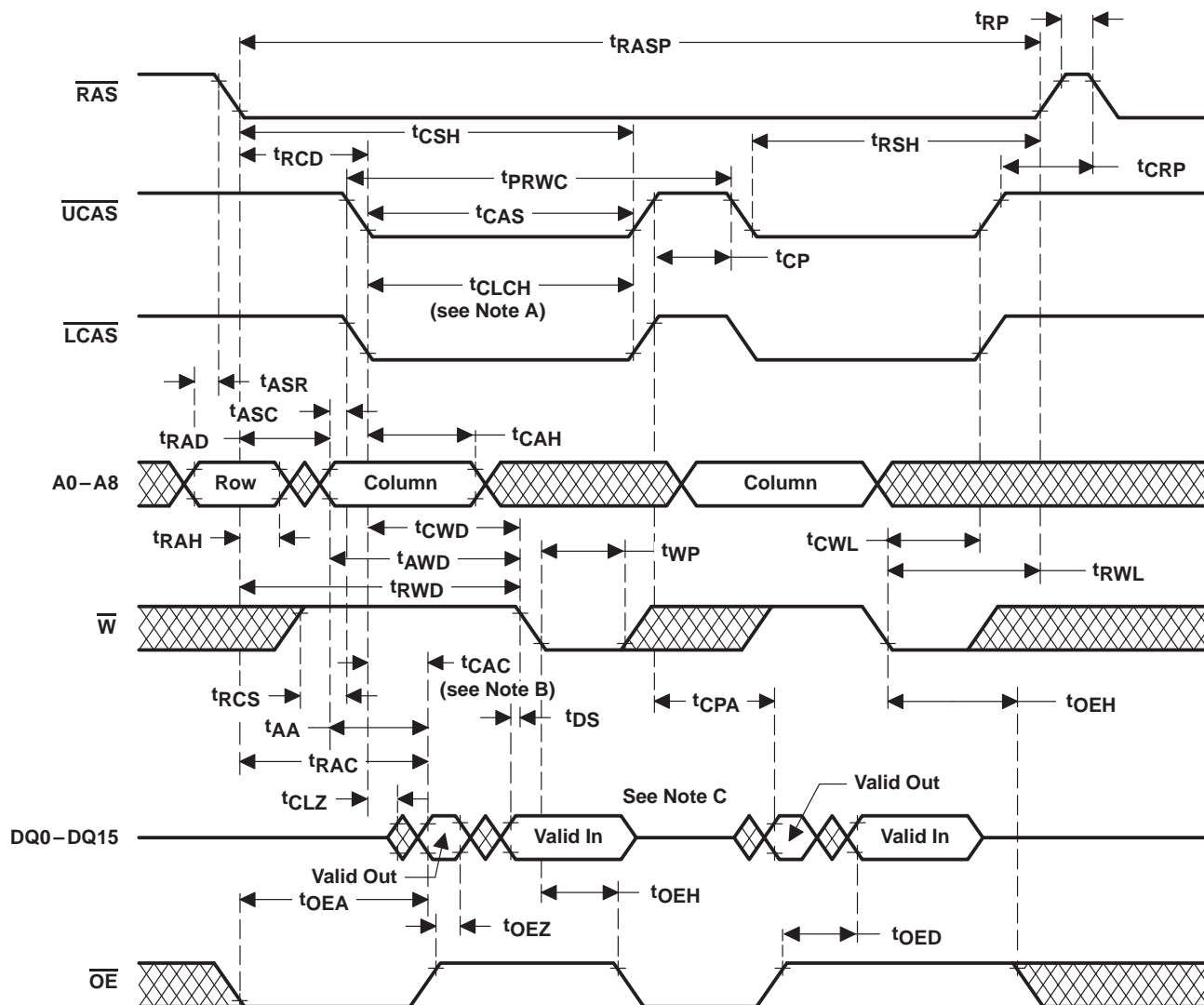
PARAMETER MEASUREMENT INFORMATION



- NOTES: A. In order to hold the address latched by the first \overline{xCAS} going low, the parameter t_{CLCH} must be met.
B. Referenced to \overline{xCAS} or \overline{W} , whichever occurs last.
C. \overline{xCAS} order is arbitrary.
D. A read cycle or read-modify-write cycle can be mixed with the write cycles as long as the read and read-modify-write timing specifications are not violated.

Figure 7. Enhanced-Page-Mode Write-Cycle Timing

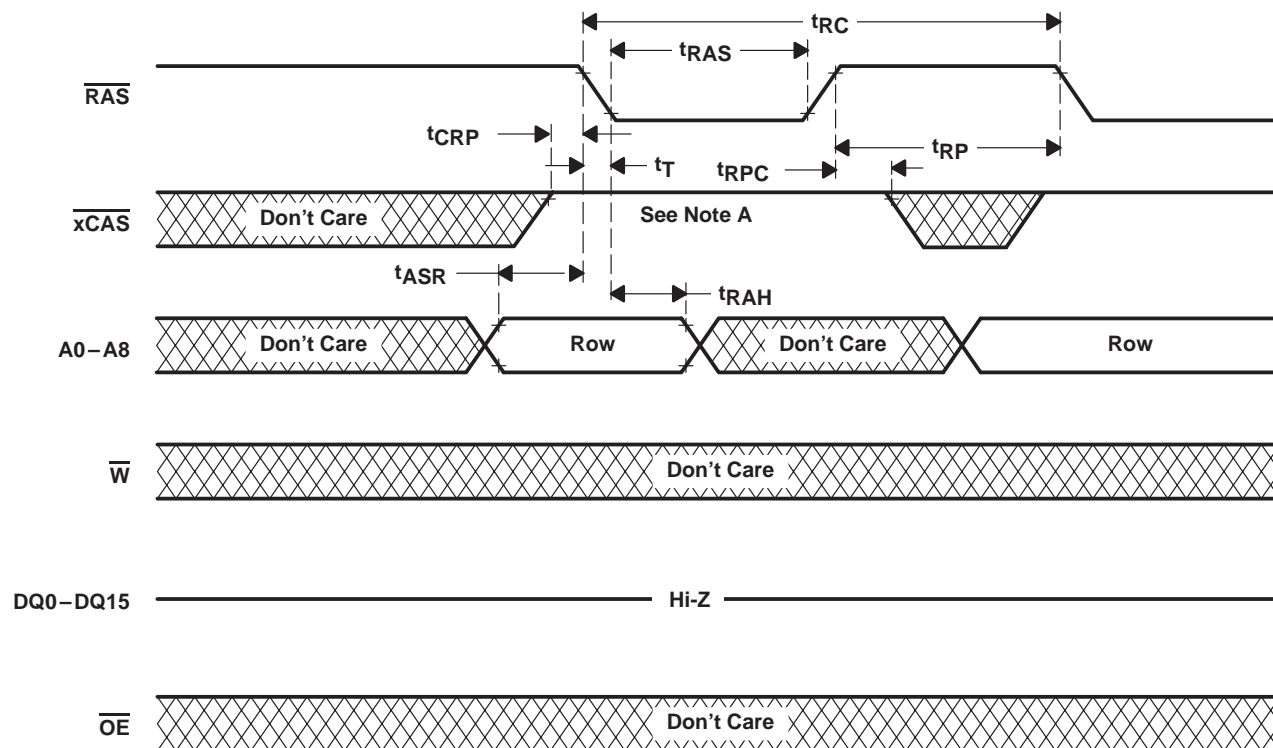
PARAMETER MEASUREMENT INFORMATION



- NOTES: A. In order to hold the address latched by the first \overline{xCAS} going low, the parameter t_{CLCH} must be met.
 B. t_{CAC} is measured from \overline{xCAS} to its corresponding DQx .
 C. Output can go from the high-impedance state to an invalid data state prior to the specified access time.
 D. \overline{xCAS} order is arbitrary.
 E. A read or write cycle can be intermixed with read-modify-write cycles as long as the read and write cycle timing specifications are not violated.

Figure 8. Enhanced-Page-Mode Read-Modify-Write-Cycle Timing

PARAMETER MEASUREMENT INFORMATION



NOTE A: All $\overline{\text{xCAS}}$ must be high.

Figure 9. $\overline{\text{RAS}}$ -Only Refresh Timing

PARAMETER MEASUREMENT INFORMATION

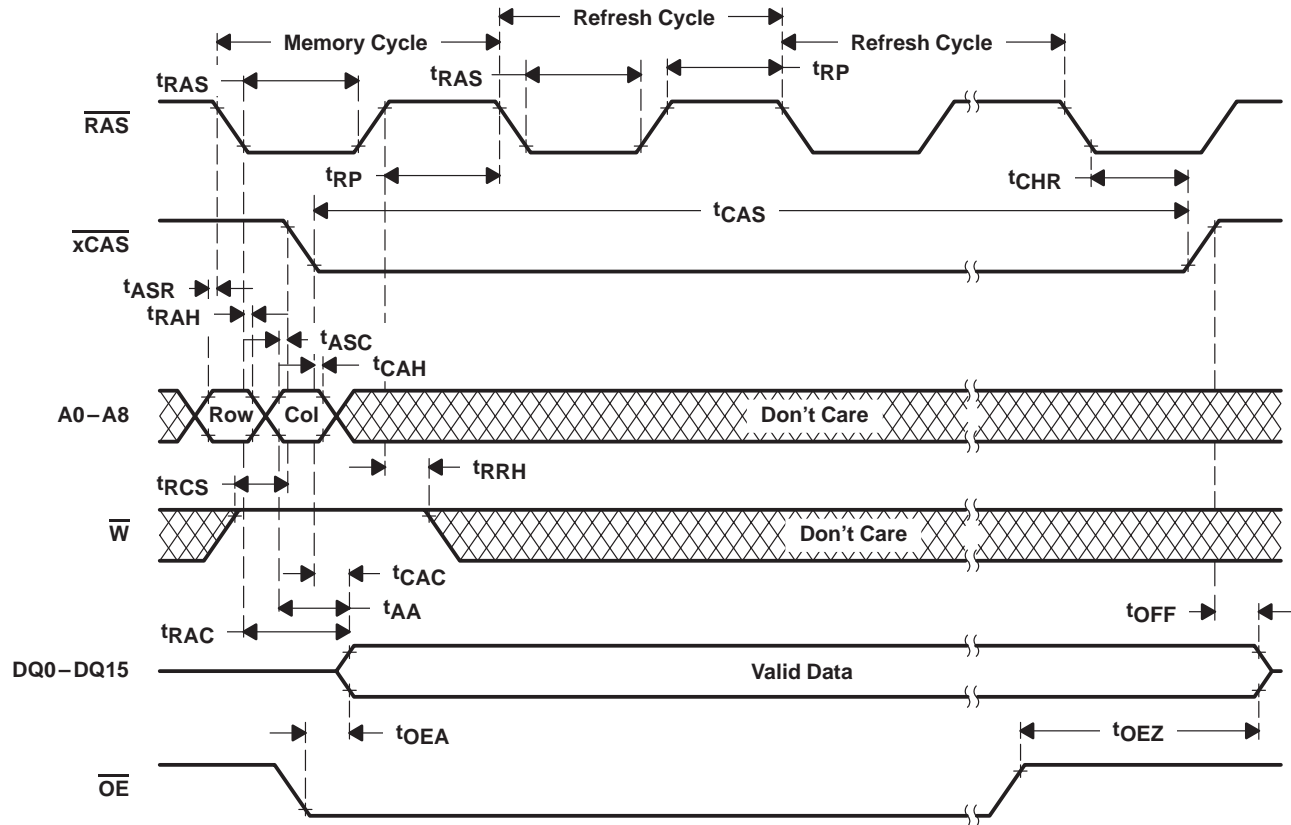
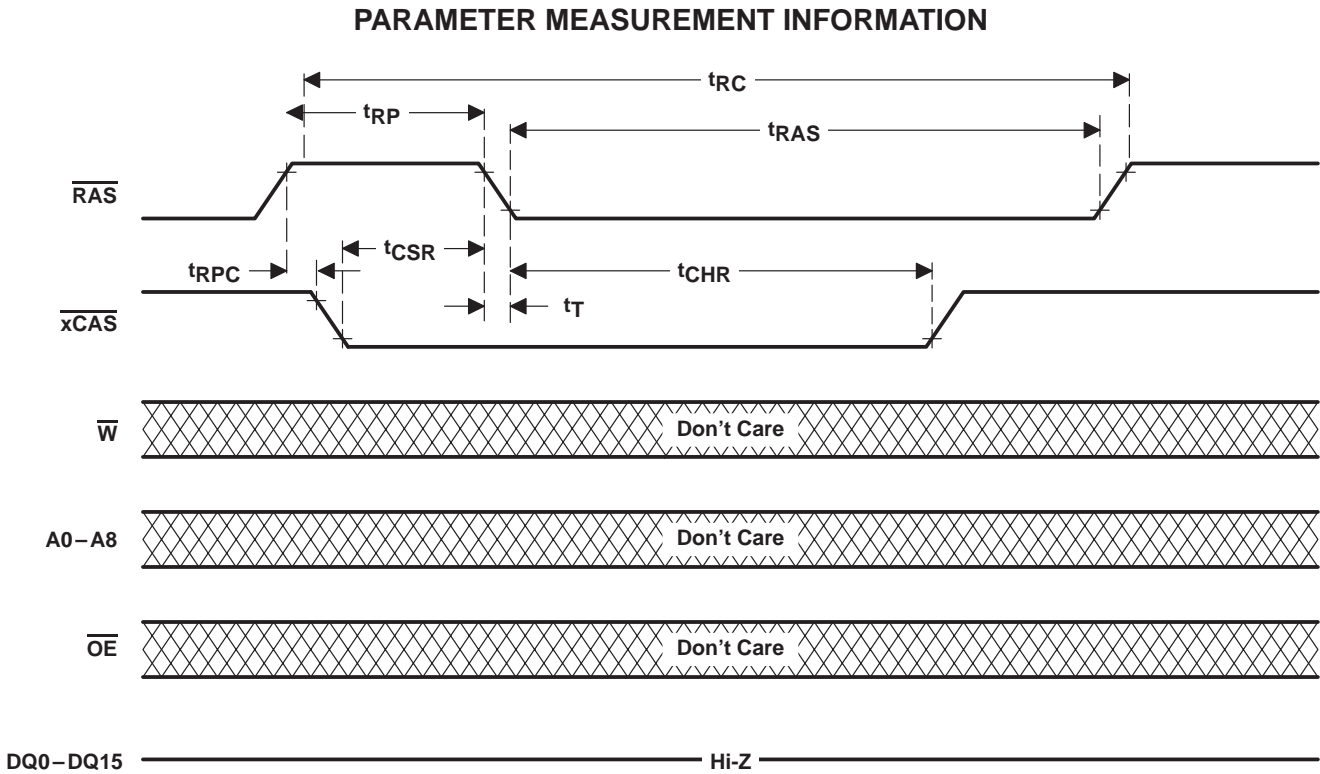


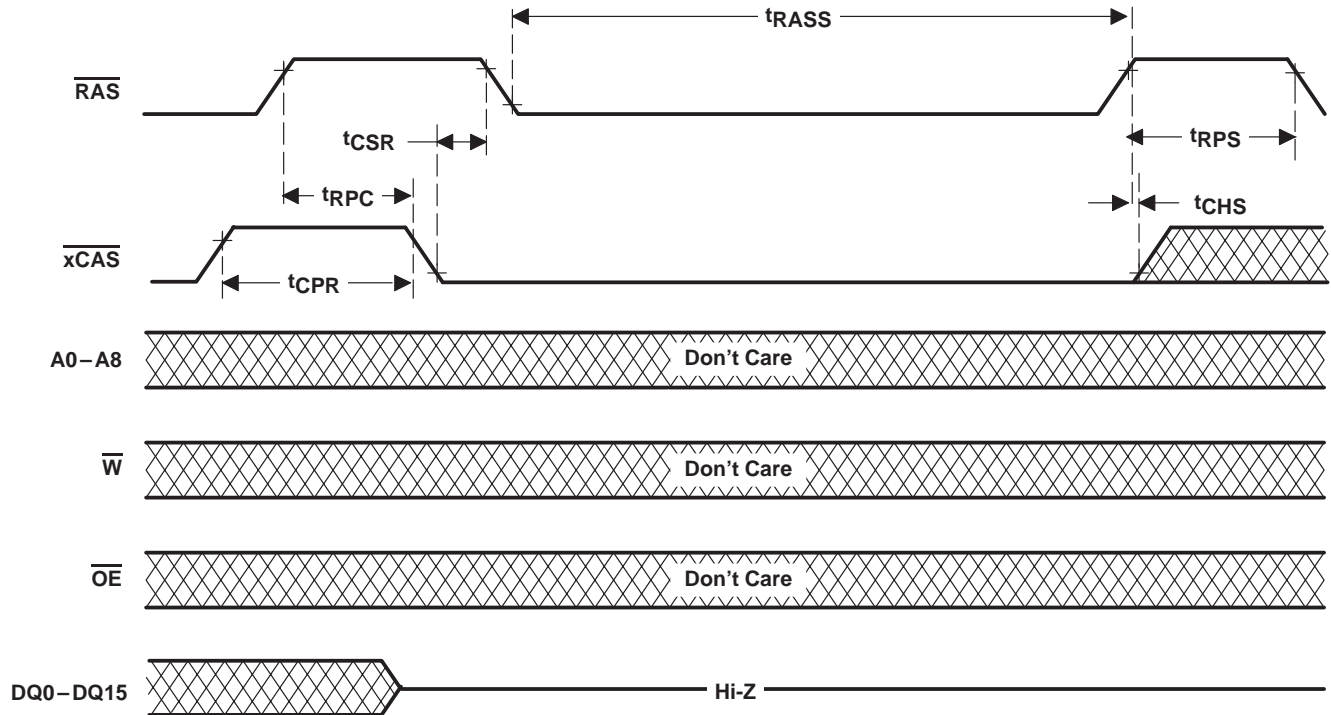
Figure 10. Hidden-Refresh-Cycle Timing



NOTE A: Any $\overline{\text{xCAS}}$ can be used.

Figure 11. Automatic-CBR- Refresh-Cycle Timing

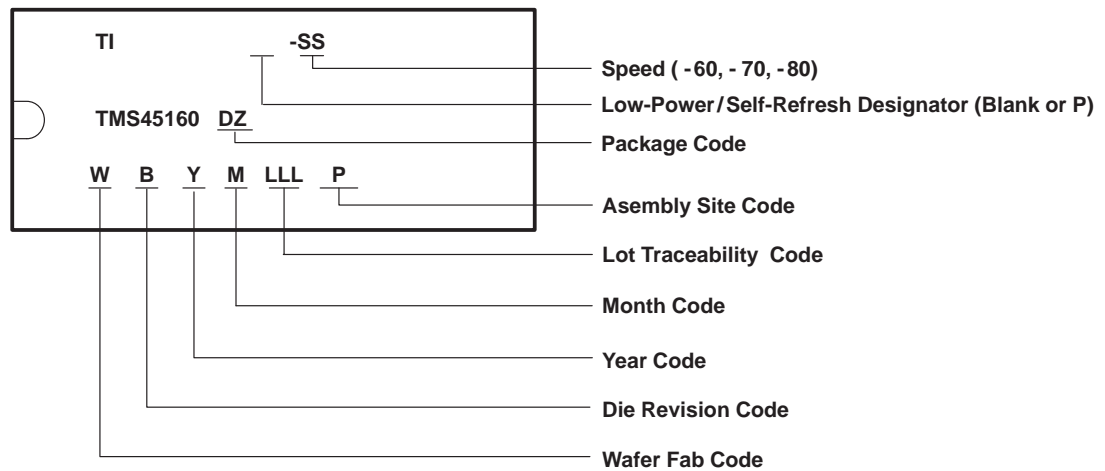
PARAMETER MEASUREMENT INFORMATION



NOTE A: Any xCAS can be used.

Figure 12. Self-Refresh-Cycle Timing

device symbolization (TMS45160 illustrated)



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